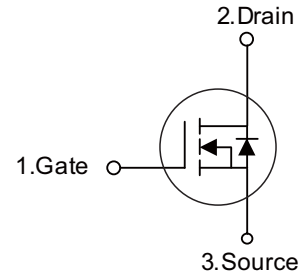


■ PRODUCT CHARACTERISTICS

VDSS	650V
$R_{DS(on)max}(@V_{GS} = 10V)$	5Ω
Qg@type	14nC
ID	2A

Symbol

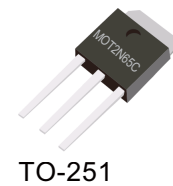
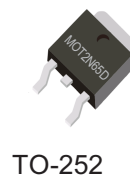


■ APPLICATIONS

- * High efficiency switch mode power supplies
- * Electronic lamp ballasts based on half bridge
- * LED power supplies

■ FEATURES

- * $R_{DS(ON)} < 5.0\Omega @ V_{GS} = 10V$
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness



■ ORDER INFORMATION

Order codes		Package	Packing
Halogen-Free	Halogen		
N/A	MOT2N65D	TO-252	2500 pieces /Reel
N/A	MOT2N65C	TO-251	70 pieces/Tube

■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ C$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	650	V
Gate-Source Voltage	V_{GSS}	± 30	V
Avalanche Current (Note 2)	I_{AR}	2.0	A
Drain Current	Continuous	I_D	2.0
	Pulsed (Note 2)	I_{DM}	8.0
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	110
Peak Diode Recovery dv/dt (Note 4)	dv/dt	4.5	V/ns
Power Dissipation	TO-251/TO-252	P_D	44
Junction Temperature	T_J	+150	$^\circ C$
Operating Temperature	T_{OPR}	-55 ~ +150	$^\circ C$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ C$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by T_J .
3. $L=55mH, I_{AS}=2.0A, V_{DD}=50V, R_G=25\Omega$, Starting $T_J = 25^\circ C$
4. $I_{SD} \leq 2.4A, di/dt \leq 200A/\mu s, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ C$

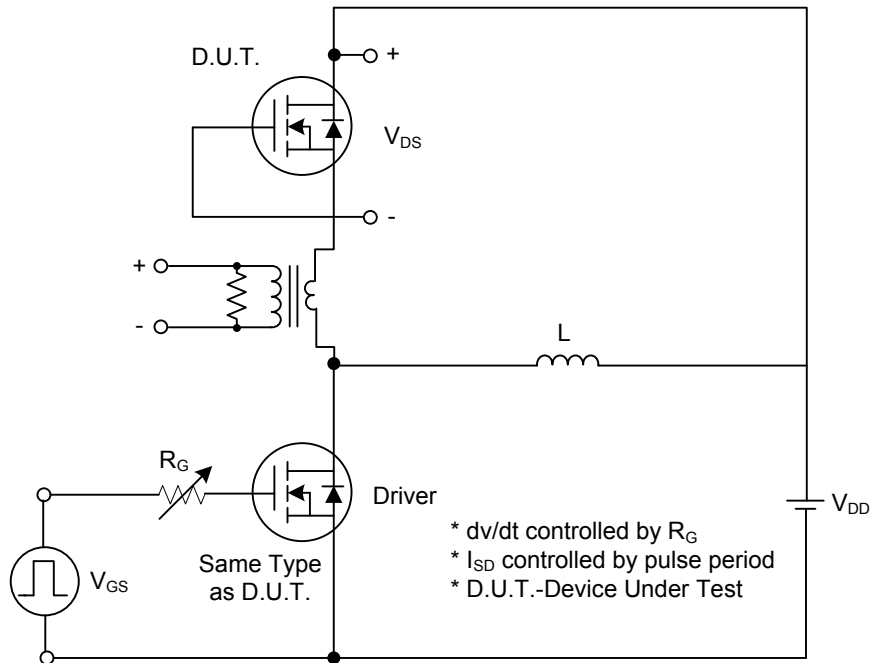


■ ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise specified)

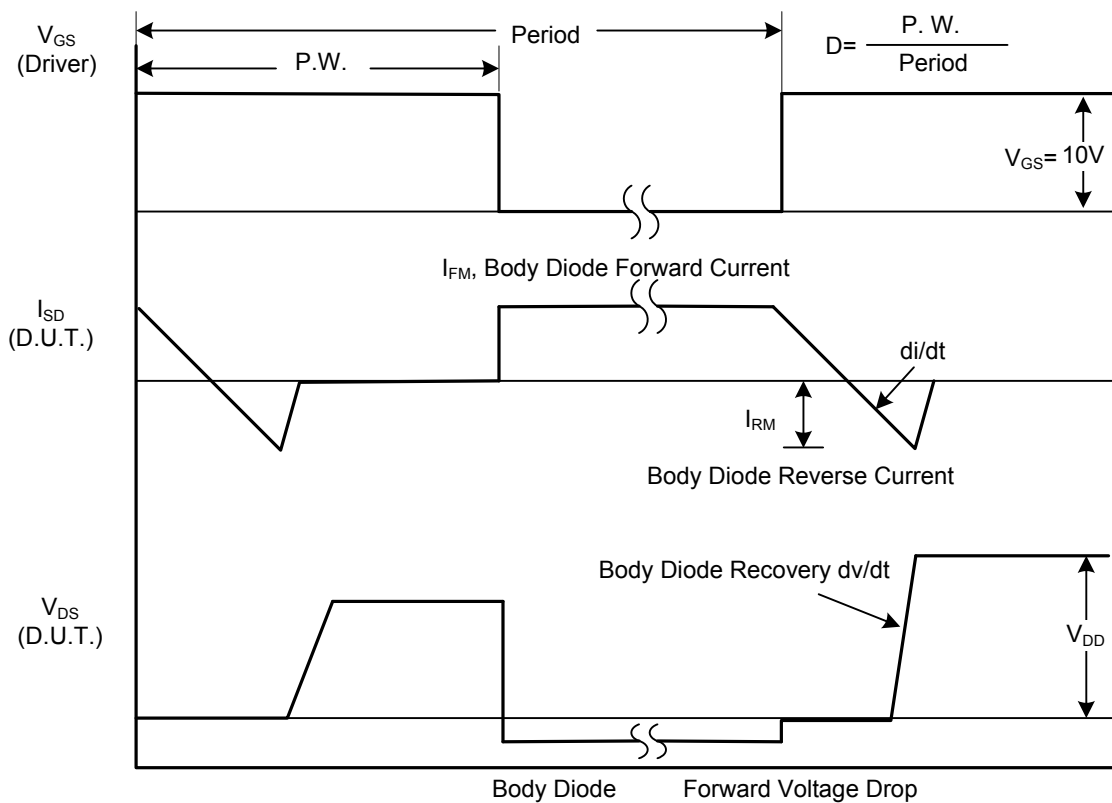
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	650			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 650V, V_{GS} = 0V$			10	μA
Gate-Source Leakage Current	Forward	I_{GSS}			100	nA
	Reverse				-100	nA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D = 250\mu A$, Referenced to 25°C		0.4		$V/^\circ\text{C}$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 1A$		3.7	5.0	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1\text{MHz}$		240	320	pF
Output Capacitance	C_{OSS}			33	45	pF
Reverse Transfer Capacitance	C_{RSS}			4.5	6	pF
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD} = 30V, I_D = 0.5A,$ $R_G = 25\Omega$ (Note 1, 2)		40	60	ns
Turn-On Rise Time	t_R			40	60	ns
Turn-Off Delay Time	$t_{D(OFF)}$			50	70	ns
Turn-Off Fall Time	t_F			22	38	ns
Total Gate Charge	Q_G	$V_{DS} = 50V, V_{GS} = 1.0V,$ $I_D = 1.3A$ (Note 1, 2)		12	14	nC
Gate-Source Charge	Q_{GS}			5.2		nC
Gate-Drain Charge	Q_{GD}			2		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_{SD} = 2.0A$			1.4	V
Continuous Drain-Source Current	I_{SD}				2.0	A
Pulsed Drain-Source Current	I_{SM}				8.0	A

- Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

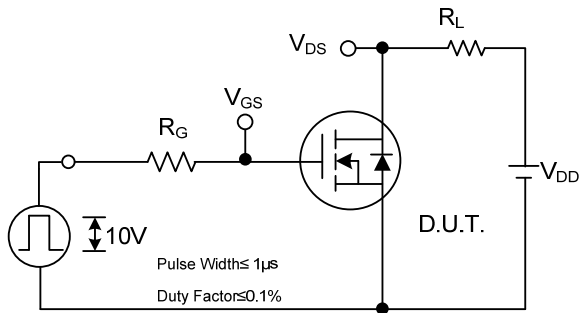


Peak Diode Recovery dv/dt Test Circuit

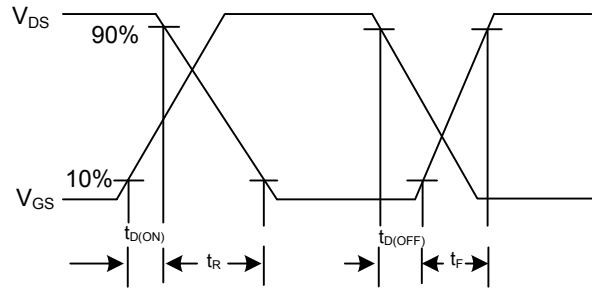


Peak Diode Recovery dv/dt Waveforms

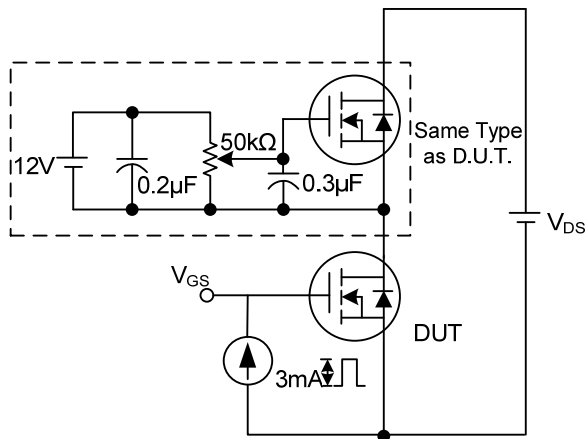
■ TEST CIRCUITS AND WAVEFORMS(Cont.)



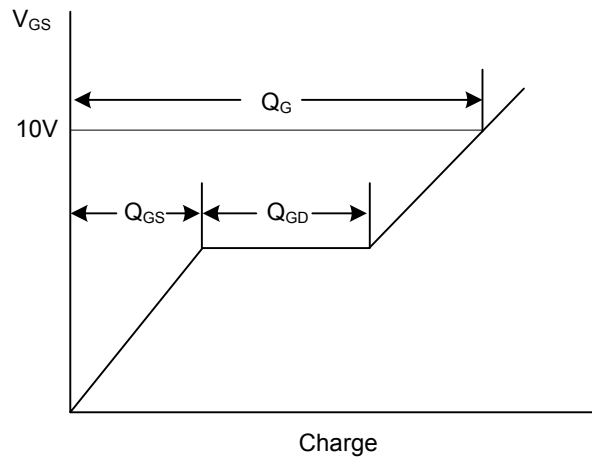
Switching Test Circuit



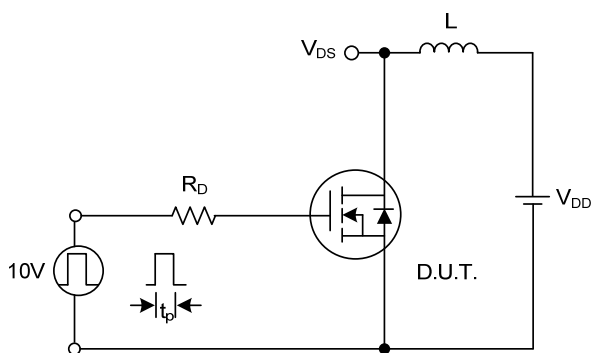
Switching Waveforms



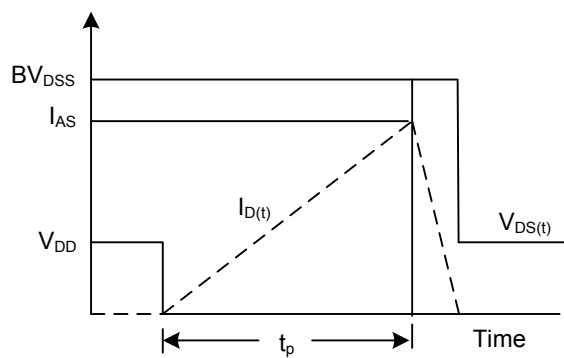
Gate Charge Test Circuit



Gate Charge Waveform

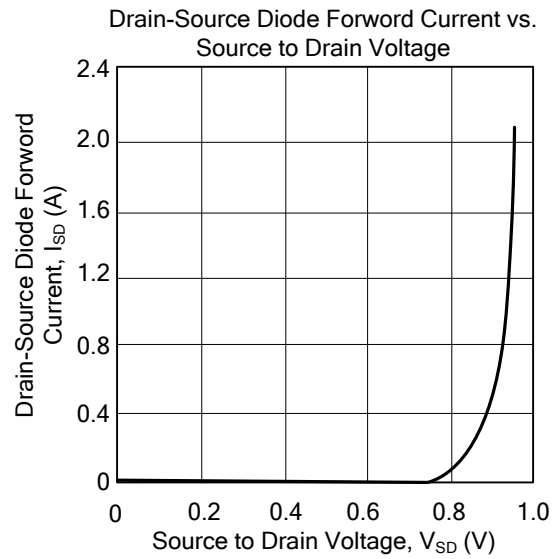
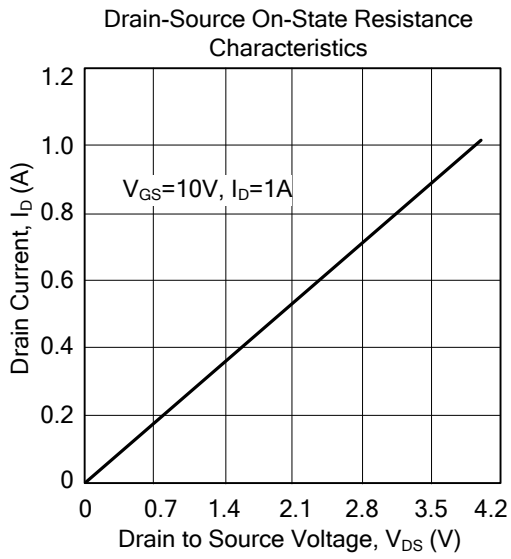
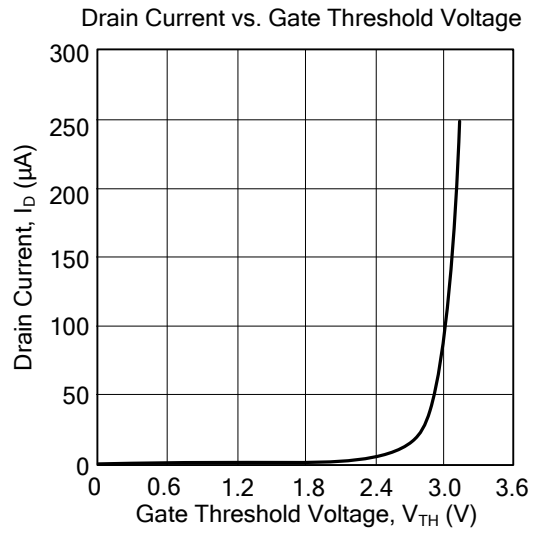
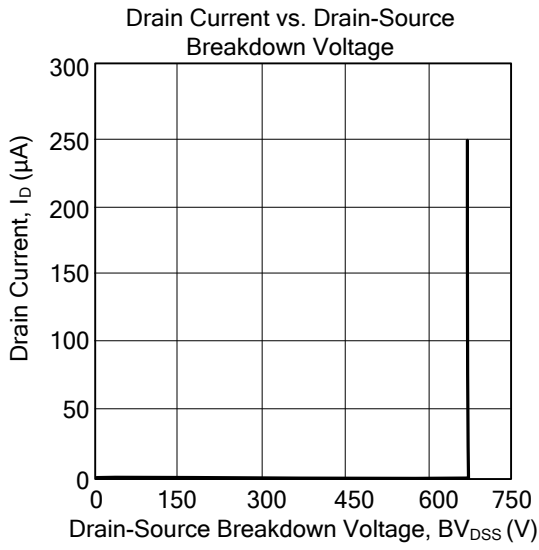


Unclamped Inductive Switching Test Circuit

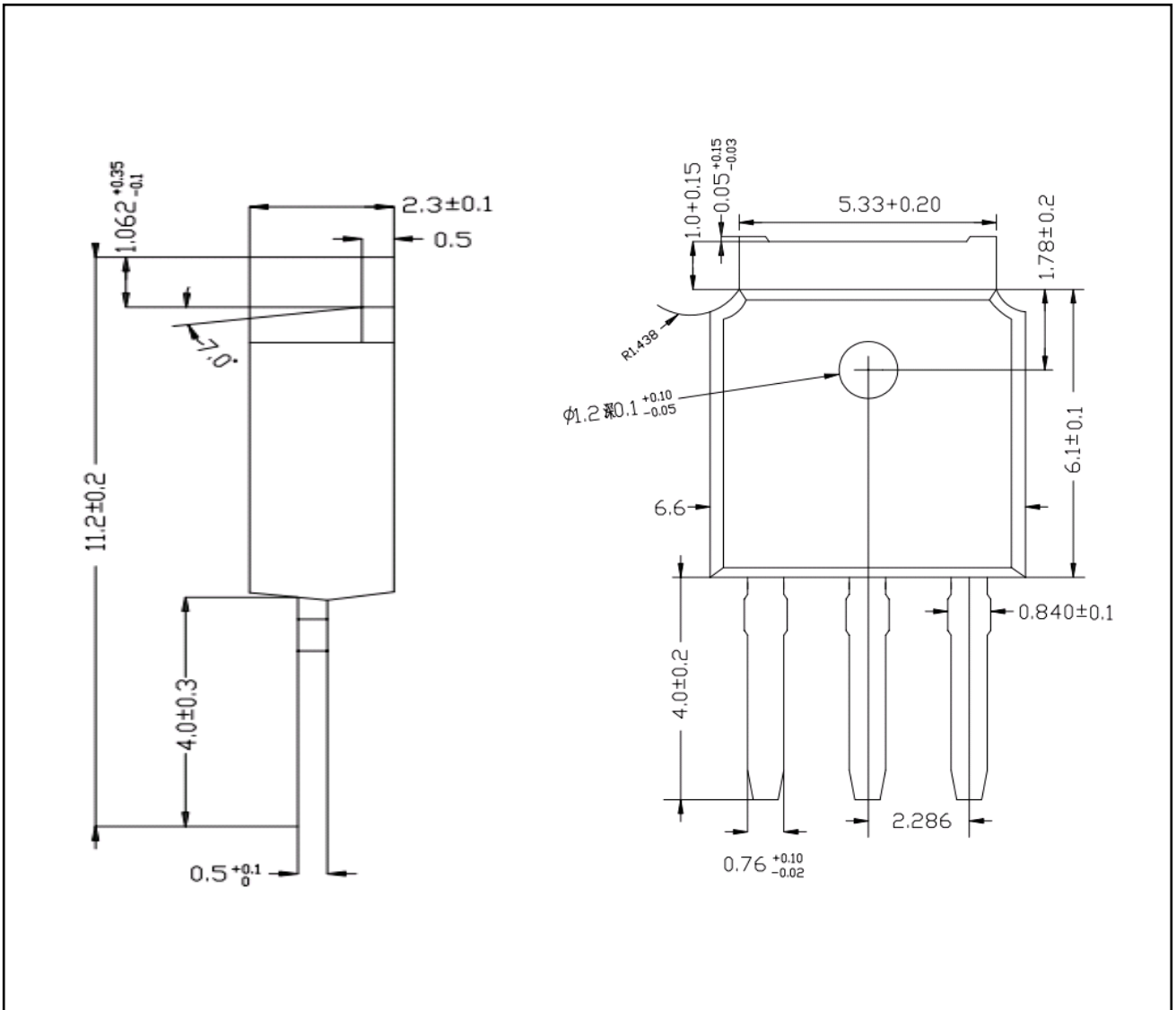


Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS



■ TO-251 PACKAGE OUTLINE DIMENSIONS



■ TO-252 PACKAGE OUTLINE DIMENSIONS

